U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	NS-5737 US	10/803,203
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	Confirmation No.
Substitute PTO Form 1449	Bulucea, Constantin	5841
	Filing Date	Group
	17 March 2004	~~2811~~ 2826

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AI						

Foreign Patent Documents

							Translation	
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	AK							

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	AN	Bohr, "Industry-Leading Transistor Performance Demonstrated on Intel's 90-nanometer Logic Process", Intel Corp., ftp://download.intel.com/research/ silicon/90nm_press_briefing-technical.pdf, 13 Aug. 2002, pp. 1 - 21
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